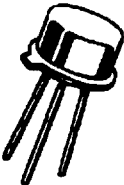


NEW ENGLAND SEMICONDUCTOR

BIPOLAR PNP TRANSISTOR TO-39/TO-5

PACKAGE	DEVICE TYPE	V _{CEO} (sus) VOLTS	I _C (max) AMPS	h _{FE} @ I _C / V _{CE} (min/max @ A/V)	V _{CE(sat)} @ I _C /I _B (V @ A/A)	P _D ** WATTS	f _T (MHz)
PNP TO-39 	2N3867	40	3	>25@2.5/3	1.3@2.5/.25	6	60
	2N3868	60	3	>20@2.5/3	1.3@2.5/.25	6	60
	2N4930	200	.05	20-200@.01/10	5@.01/.001	5	10 ^t
	2N4931	250	.05	20-200@.01/10	5@.01/.001	5	10 ^t
	2N5091	300	1	20-200@.1/15	3@.025/.0025	4	10 ^t
	2N5093	350	1	20-200@.1/15	3@.025/.0025	4	10 ^t
PNP TO-5 	2N5094	400	1	20-200@.1/15	3@.025/.0025	4	10 ^t
	2N5096	450	1	20-200@.1/15	3@.025/.0025	4	10 ^t
	2N5149	80	2	70-200@1/5	.85@2/.2	6	60
	2N5151	80	5	30-90@2.5/5	.75@2.5/.25	10	60
	2N5153	80	5	70-200@2.5/5	.75@2.5/.25	10	60
	2N5415	200	1	30-150@.05/10	2.5@.05/.005	10	15
	2N5416	300	1	30-150@.05/10	2@.05/.005	10	15
	2N6193	100	1	60-240@2/2	0.7@2/.2	10	30

** T_C = 100°C

^h V_{CER}

^t Typical